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13. ABSTRACT (Maximum 200 words) A new materials arena has been opened for quantum electron transport devices based on magnetic, semi-metal compound semiconductor heterostructures. Epitaxial ultrathin films of a rare earth arsenide, ErAs, were grown in GaAs semiconductors. The dissimilarities between the ErAs, a magnetic semimetal, and the compound semiconductor make possible the fabrication of three terminal resonant tunneling transistors with ultra thin semi-metal quantum wells. Resonant tunneling through semi-metal quantum wells was observed for the first time. A strong coupling of the magnetization and the resonant tunneling was discovered that demonstrates magnetization controlled resonant tunneling. Nano-composites of ErAs / GaAs were also grown. Electron transport in these systems exhibits giant magneto-resistance, magnetization controlled island to island electron hopping transport. This research program has opened the possibility of high density, non-volatile information storage and processing based on magnetic, semi-metallic, quantum structures grown and integrated into compound semiconductor heterostructures.				
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Final Report

F49620-93-329 "Resonant tunneling and hot electron spectroscopy in buried rare-earth arsenide/semiconductor heterostructures" and

AASERT F49620-93-0440 "Non-linear terahertz electronics with self organized rare-earth arsenide semi-metal/semiconductor composites".

The rare-earth arsenides are magnetic, semimetallic compounds that can be grown epitaxially on III-V compound semiconductors like GaAlAs. These systems open the potential for novel electronics and photonics based on magnetic, semimetal semiconductor heterostructures. The objective of this work was to explore the magnetics, transport and optics and assess the importance of this material system in future magnetics, electronics and photonics.

The technical approach followed several avenues.

1. Three terminal resonant tunneling diodes comprised of ErAs quantum wells in AlGaAs heterostructures were successfully grown, fabricated and tested.
2. Nano-composites of ErAs islands were successfully grown and used to explore magnetization controlled island - island hopping transport.
3. ErAs islands were imbedded in highly doped 2-dimensional electron gases to control electron percolation and produce random, self organized quasi-optical Schottky diode arrays for terahertz harmonic generation.
4. Near IR photo response of ErAs / GaAs nano-composites was measured to assess the potential for fast fast photo-conductive detectors.

The following milestones and breakthroughs were achieved.

- The contrasting electrical, chemical and structural properties of the ErAs and III-V semiconductors allows ion implant isolation of buried ErAs semimetal from the doped host semiconductor. Followed by contact anneal, selective and specific ohmic contact can be made to ultra thin buried semi-metal layers in semiconductor heterostructures. A simple and effective method fabricating three terminal resonant tunneling diodes follows.
- Resonant tunneling through semimetal quantum wells was observed for the first time.
- Using the unique properties of these three terminal resonant tunneling diodes, it was discovered that electrons tunnel through resonant hole channels in the ErAs quantum well resonant tunneling diodes.
- The dispersion relation of the resonant hole channels was measured.

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- A giant spin splitting of the resonant channel was discovered and is understood to be caused by the exchange interaction between the Er 4f spins and the resonant hole channel.

- Following measurements of the hole dispersion we are able to measure the dispersion of the exchange coupling of the Er 4f spins and the resonant holes.

- ErAs islands can be grown with sizes controlled by the growth temperature of the substrate. Superlattices of 2-dimensional sheets ErAs islands can be grown.

- A giant negative magnetoresistance was discovered that points to magnetization controlled hopping conduction between islands.

- Terahertz harmonic generation from self organized Schottky diode arrays has been measured. The predicted enhancement is not observed.

- Preliminary measurements on the near IR photo response indicate that the internal photoemission in ErAs / GaAs nanocomposites may over another route to fast near IR photo detectors

Three terminal resonant tunneling diodes. Ion implantation has little effect on the electrical properties of ultra thin semi-metals. As a result regions of the surrounding III-V semiconductor can be rendered insulating leaving a thin ($>0.8\text{nm}$) protruding metallic sheet. (Fig. 1.) (It was discovered in earlier work that because of the peculiarities of the band structure of ErAs there was no semi-metal to semiconductor transition at thicknesses down to 3 monolayers.) Ohmic contact to this sheet leaves a three terminal device in which the control electrode can be as thin as 0.8nm . An abiding materials problem, however, is the

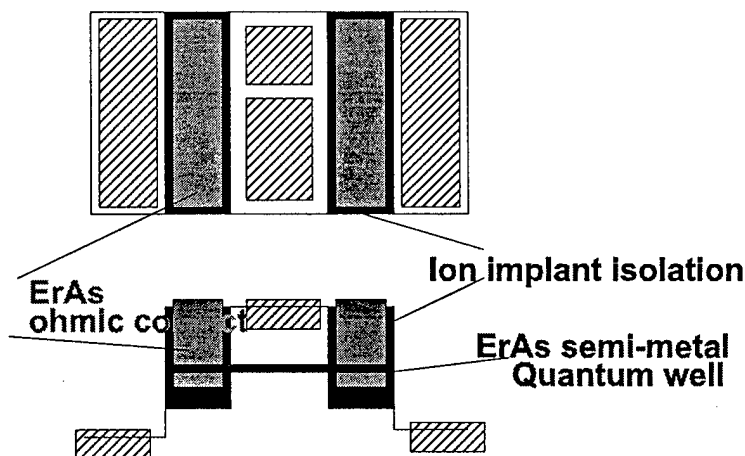


Fig. 1 Ion implantation can render doped regions of the heterostructure insulating without altering the conductivity of ultra-thin buried metal layers.

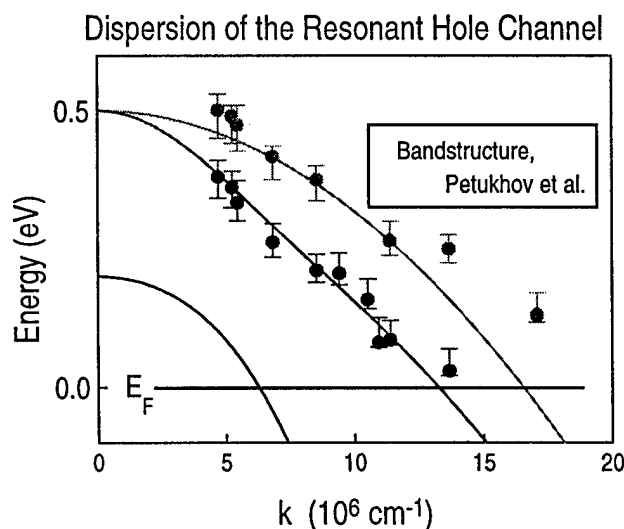


Fig. 2 The dispersion of the hole channels determined from the thickness dependence of the quantum well potential for resonant tunneling.

quality of the III-V semiconductor grown on top of the rare earth arsenide (ReAs). As a result, while the semi-metal quantum well can be contacted and used to determine the potential in the quantum well, it is difficult to isolate it from the top III-V epilayers. None the less, the semimetal quantum well enables one to define and measure the Fermi energy. This is not possible in conventional III-V heterostructures.

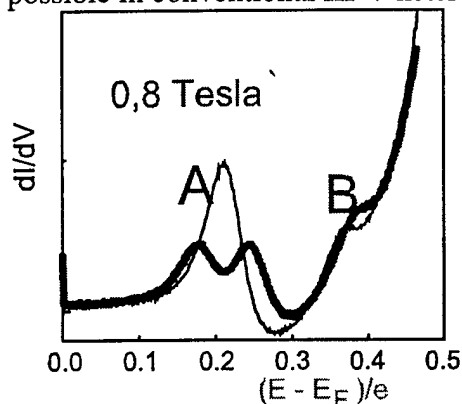


Fig. 3 The resonant channels are distinguished by their dependence on magnetic field.

Two resonant channels were identified and distinguished by their behavior in a magnetic field. Remarkably, a systematic study of the dependence on the quantum well thickness revealed that the resonant channels were hole channels and their dispersion was measured. (Fig. 2)

In modest magnetic fields, a large splitting of the channels was observed which depended on the orientation of the magnetic field. (Fig. 3.) The splitting was measured to be of the order of .1 eV or $\sim 1000\text{K}$. It is caused by the exchange interaction between the 4f spin and the resonant hole states.

By measuring the splitting as a function of the thickness, the dispersion or wave vector dependence of the exchange coupling could be determined. It appears to vanish as k approaches 0. This is expected since the states

at $k=0$ are predominately on the As and the contact exchange interaction with the 4f spin should be suppressed.

This research points to the possibility of fabricating a device in which the resonant tunneling is controlled by the orientation of the magnetization of a ferromagnetic film.

Growth of ErAs / GaAs nanocomposites.

Below 3 monolayers of ErAs the material forms islands. The island size has been found to be determined by the substrate temperature. Around 600 C the islands are of the order of 2 nm, whereas at growth temperatures approaching 700 C the islands are nearing 100 nm. (Fig. 4)

Giant magneto resistance and magnetization controlled island hopping. Resistivity measurements at low temperature in a magnetic field reveal a striking negative magneto-resistance. For some nano-composites the resistance drops some 4 orders of magnitude in a 2 Tesla field. (Fig. 5) Theoretical models developed by Petukhov et al. point to size dependent magnetization fluctuation characteristic of nanometer scale paramagnetic particles. The relative orientation determines the hopping rate. More needs to be done establish the mechanism and its dependence on material parameters.

Nano-composites of ErAs / GaAs with doping layers appear like random Schottky diode arrays. Enhanced non-linearity's are expected from two different perspectives. At percolation

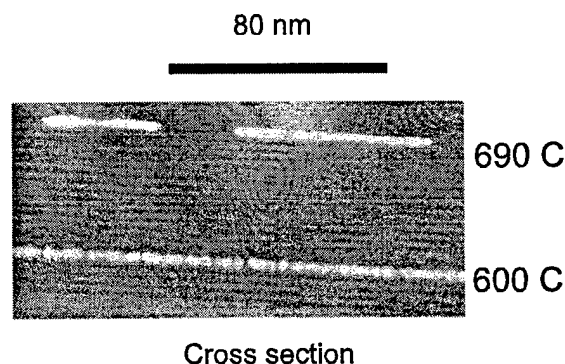


Fig. 4 ErAs island depends on substrate temperature.

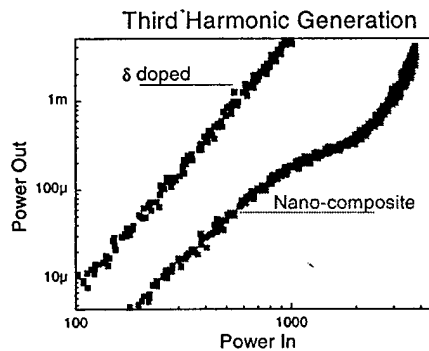


Fig. 6 Terahertz third harmonic generation (600 GHz in 1.8 THz out) from a doped layer and a doped layer with ErAs semi-metal islands.

diodes that should be intrinsically non-linear.

Early results are not encouraging. The insertion of the semi-metal islands in an otherwise uniform 2 dimensional electron gas results in lower non-linear response. (Fig. 6).

Near IR Photoresponse. Internal photoemission from small ErAs metal particles could lead to fast sensitive near IR photo detectors. They have the same features as does LT GaAs with the As semi-metal cluster replaced by the ErAs. The spectrum of the photo response shows threshold consistent with internal photo-emission from the ErAs particles and that is consistent with the accepted Schottky barrier heights between ErAs and GaAs. Preliminary measurements on the time response find it fast enough to warrant further investigation.

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non-linearity's should be amplified by the strong electric fields that appear at the constrictions. From another perspective we have an array of back to back Schottky

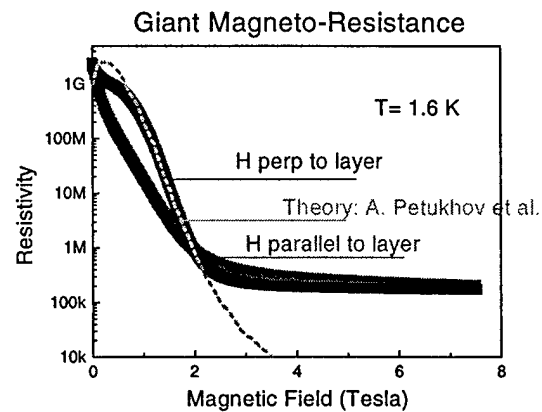


Fig. 5 A giant negative magneto-resistance signals magnetization controlled hopping transport between the islands.

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Personnel participation in this contract:

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K. Zhang	Post-doctoral researcher	EG&G
S.-P. Chau	Undergraduate researcher	EG&G
D.E. Brehmer	Graduate student researcher	Writing dissertation
D. Schmidt	Graduate student researcher	Research in progress
S. Rausch	Diploma student, Karlsruhe (without salary support)	Writing Diploma-arbeit
James Ibbetson	Post-doctoral researcher (without salary support)	Continuing
Frank Hegmann	Post-doctoral researcher	University of Alberta
C. Palmstrom	Consultant	Faculty, U. Minnesota